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### US Patent Class 257-- ACTIVE SOLID-STATE DEVICES (EG, TRANSISTORS ...

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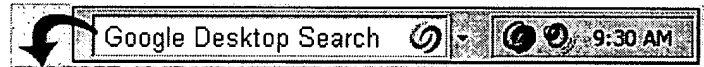
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L12    20040084721 A1    1006204    L12

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*DB=PGPB; PLUR=YES; OP=OR*

L5 L3 and substrate 1 L5

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<u>L9</u>	EP 1073110 A1	3345430	<u>L9</u>
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<u>L7</u>	JFET and "field shield"	2	<u>L7</u>
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<u>L5</u>	L3 and substrate	1	<u>L5</u>
<u>L4</u>	L3 asnd substrate	253022	<u>L4</u>
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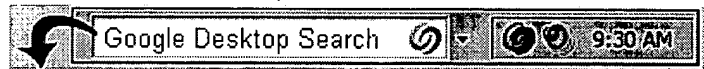
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